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# MBRJ2045CTG

## Product Preview SWITCHMODE Power Rectifier

### Features and Benefits

- Low Forward Voltage
- Low Power Loss / High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- This is a Pb-Free Device

### Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B  
Machine Model = C

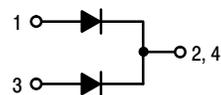
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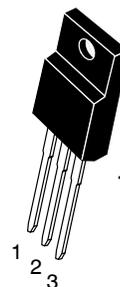
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## SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 45 VOLTS



### MARKING DIAGRAM



TO-220 FULLPAK™  
CASE 221AH  
CT SUFFIX



A	= Assembly Location
Y	= Year
WW	= Work Week
G	= Pb-Free Package
AKA	= Diode Polarity

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MBRJ2045CTG

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	45	V
Average Rectified Forward Current Per Device Per Diode ( $T_C = 165^\circ\text{C}$ )	$I_{F(AV)}$	20 10	A
Peak Repetitive Forward Current per Diode Leg (Square Wave, 20 kHz, $T_C = 163^\circ\text{C}$ )	$I_{FRM}$	20	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	150	A
Peak Repetitive Reverse Surge Current (2.0 $\mu\text{s}$ , 1.0 kHz) See Figure 11	$I_{RRM}$	1.0	A
Storage Temperature Range	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature (Note 1)	$T_J$	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance - Junction-to-Case - Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	4.3 105	$^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (Note 2) ( $i_F = 10$ Amps, $T_J = 125^\circ\text{C}$ ) ( $i_F = 20$ Amps, $T_J = 125^\circ\text{C}$ ) ( $i_F = 20$ Amps, $T_J = 25^\circ\text{C}$ )	$V_F$	-	0.50 0.67 0.71	0.57 0.72 0.84	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ )	$i_R$	-	10.4 0.02	15 0.1	mA

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

## DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping <sup>†</sup>
MBRJ2045CTG	TO-220FP (Pb-Free)	50 Units / Rail

# MBRJ2045CTG

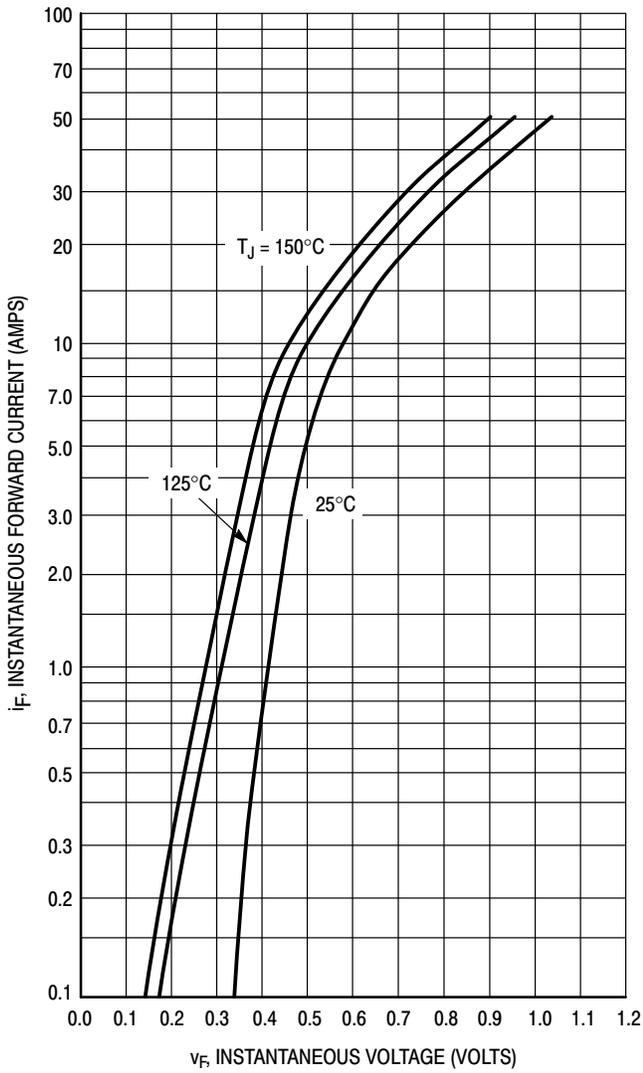


Figure 1. Typical Forward Voltage

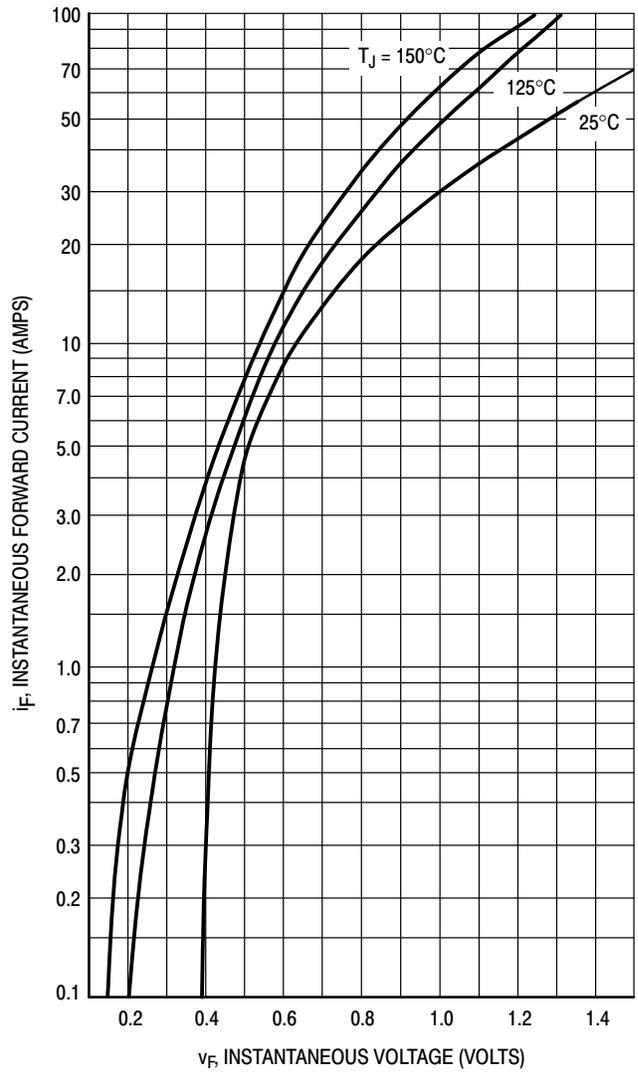


Figure 2. Maximum Forward Voltage

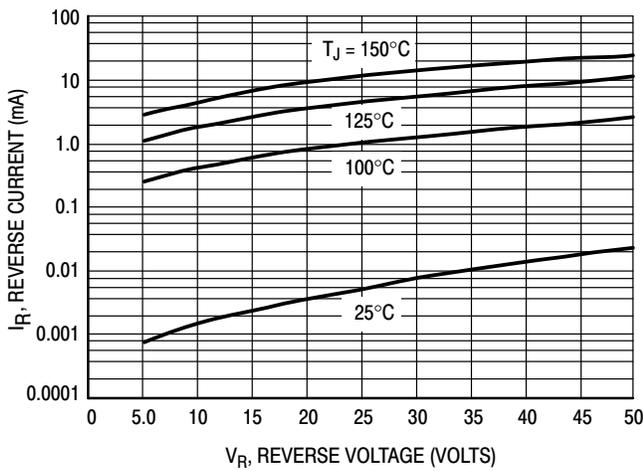


Figure 3. Typical Reverse Current

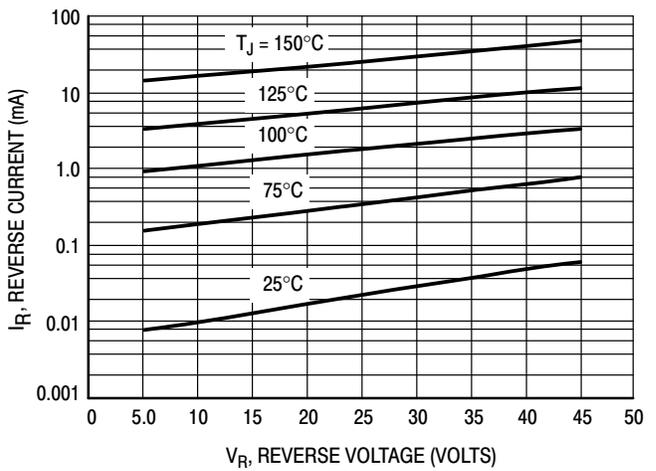


Figure 4. Maximum Reverse Current

# MBRJ2045CTG

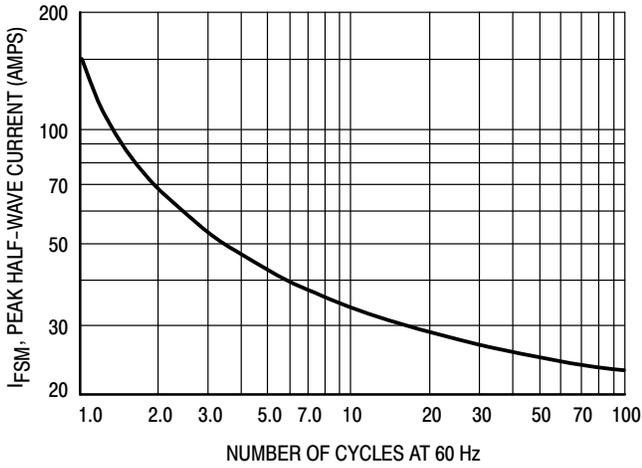


Figure 5. Maximum Surge Capability

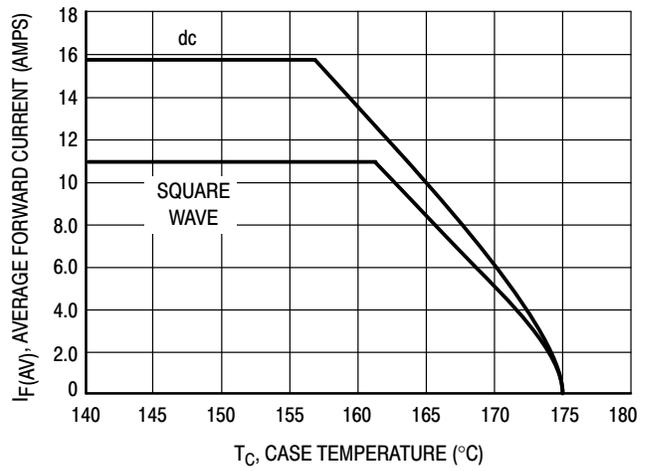


Figure 6. Current Derating, Case, Per Leg

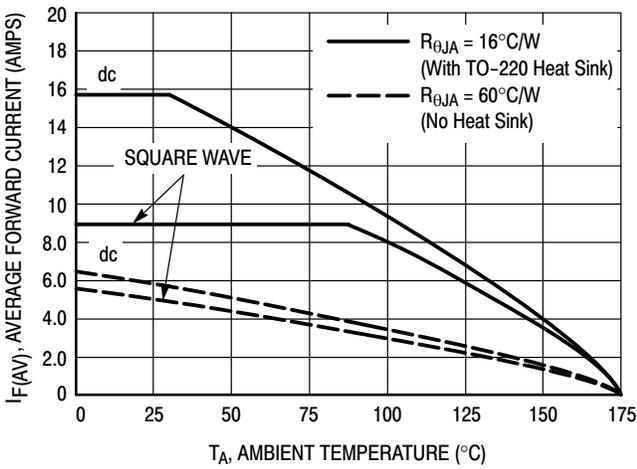


Figure 7. Current Derating, Ambient, Per Leg

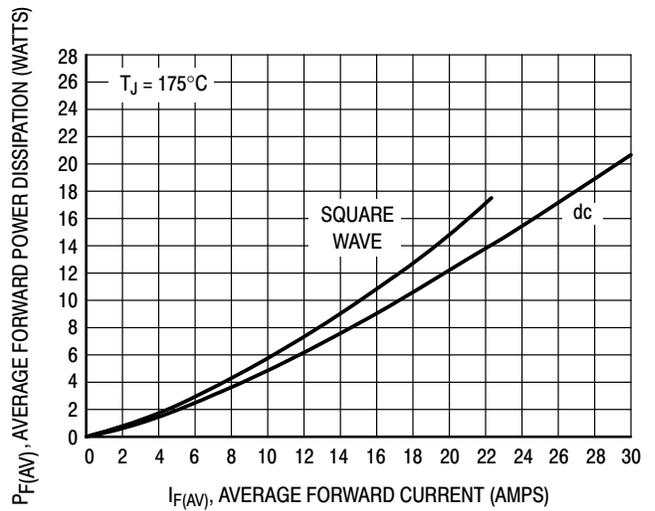


Figure 8. Forward Power Dissipation

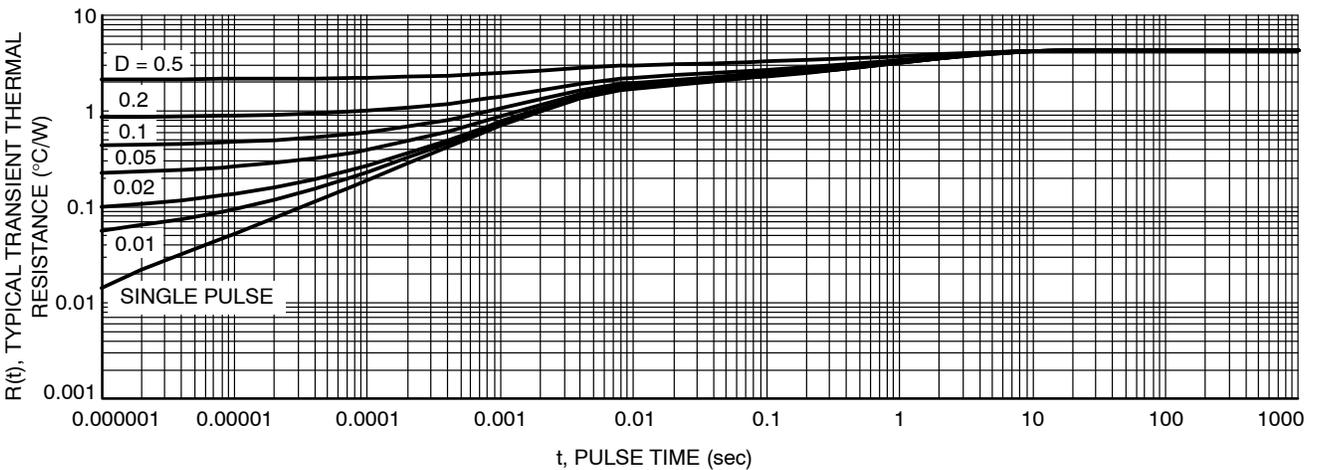
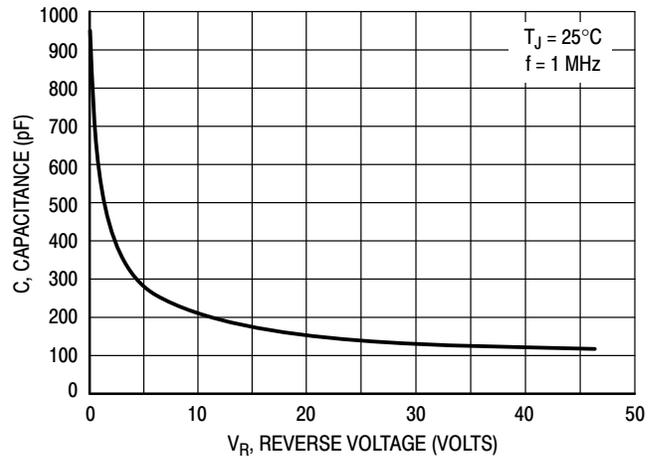


Figure 9. Typical Transient Thermal Response, Junction-to-Case

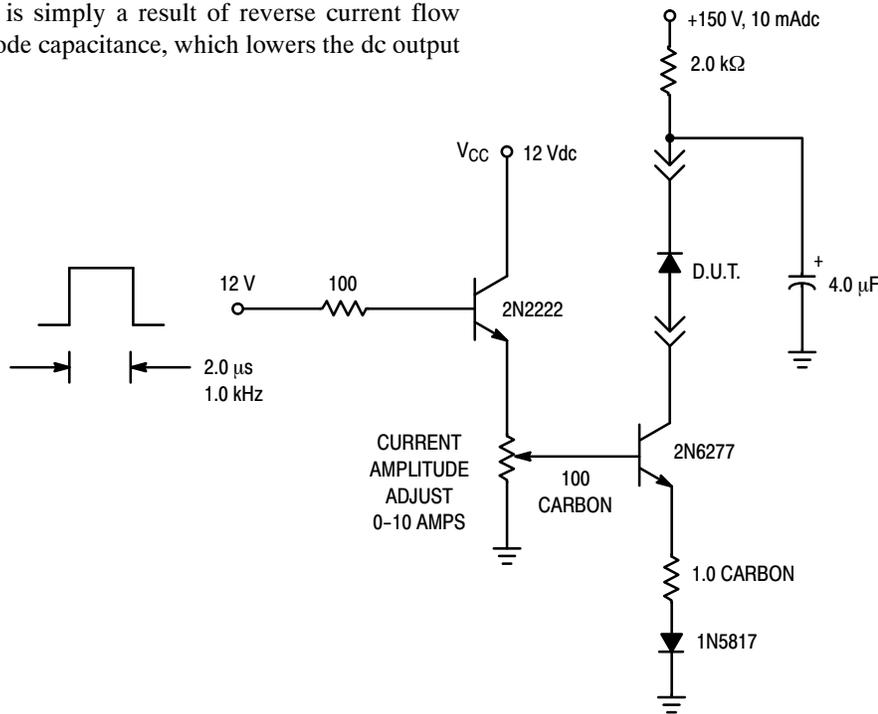
**HIGH FREQUENCY OPERATION**

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 10.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 percent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.



**Figure 10. Typical Capacitance**

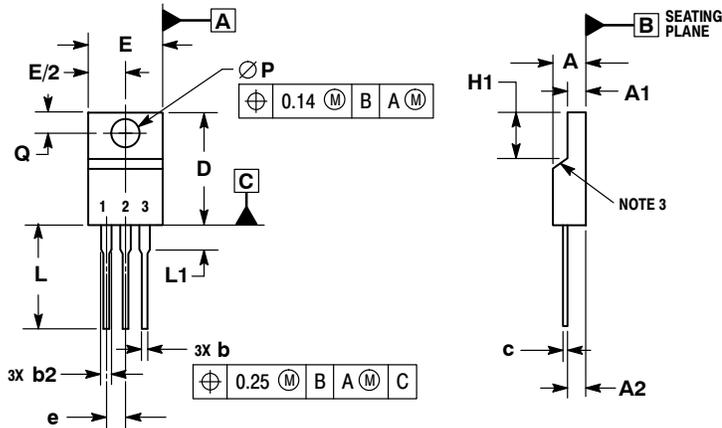


**Figure 11. Test Circuit for dv/dt and Reverse Surge Current**

# MBRJ2045CTG

## PACKAGE DIMENSIONS

### TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

DIM	MILLIMETERS	
	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.70
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.70	7.10
L	12.70	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

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